# Supertex inc.



# N-Channel Enhancement-Mode Vertical DMOS FET

## **Features**

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C<sub>ISS</sub> and fast switching speeds
- Excellent thermal stability
- Integral source-drain diode
- High input impedance and high gain

## Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

## **General Description**

This enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## **Ordering Information**

Device	Package Option TO-92	BV <sub>DSS</sub> /BV <sub>DGS</sub> (V)	R <sub>DS(ON)</sub> (max) (Ω)	I <sub>D(ON)</sub> (min) (A)	
VN1206	VN1206L-G	120	6.0	1.0	

-G indicates package is RoHS compliant ('Green')



## Pin Configuration



### **Product Marking**



Package may or may not include the following marks: Si or 🎧

#### TO-92 (L)

# Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV <sub>DSS</sub>
Drain-to-gate voltage	BV <sub>DGS</sub>
Gate-to-source voltage	±30V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Distance of 1.6mm from case for 10 seconds.

## **Thermal Characteristics**

Package	I <sub>D</sub> (continuous) <sup>†</sup> (mA)	Ι <sub>D</sub> (pulsed) (A)	Power Dissipation @T <sub>c</sub> = 25°C (W)	θ <sub>jc</sub> (°C/W)	<b>θ</b> <sub>ja</sub> (°C/W)	l <sub>DR</sub> † (mA)	l <sub>DRM</sub> (A)
TO-92	230	2.0	1.0	125	170	230	2.0

Notes:

 $\dagger$  I<sub>D</sub> (continuous) is limited by max rated T<sub>i</sub>.

### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise specified)

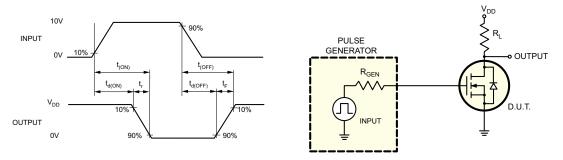
Sym	Parameter	Min	Тур	Max	Units	Conditions	
BV	Drain-to-source breakdown voltage	120	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 100µA	
V <sub>GS(th)</sub>	Gate threshold voltage	0.8	-	2.0	V	$V_{GS} = V_{DS}, I_{D} = 1.0 \text{mA}$	
I <sub>GSS</sub>	Gate body leakage	-	-	100	nA	$V_{GS}$ = ±15V, $V_{DS}$ = 0V	
			-	10		$V_{GS}$ = 0V, $V_{DS}$ = Max Rating	
I <sub>DSS</sub>	Zero gate voltage drain current	-	-	500	μA	$V_{DS} = 0.8Max$ Rating, $V_{GS} = 0V$ , $T_A = 125^{\circ}C$	
I <sub>D(ON)</sub>	On-state drain current	1.0	-	-	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V	
Б	Static drain-to-source on-state resistance	-	-	10	Ω	$V_{_{\rm GS}}$ = 2.5V, I <sub>D</sub> = 100mA	
R <sub>DS(ON)</sub>		-	-	6.0		$V_{GS} = 10V, I_{D} = 500mA$	
G <sub>FS</sub>	Forward transductance	300	-	-	mmho	V <sub>DS</sub> = 10V, I <sub>D</sub> = 500mA	
C <sub>ISS</sub>	Input capacitance	-	-	125		V <sub>GS</sub> = 0V,	
C <sub>oss</sub>	Common source output capacitance	-	-	50	pF	$V_{\rm DS} = 25V,$	
C <sub>RSS</sub>	Reverse transfer capacitance	-	-	20		f = 1.0MHz	
t,	Rise time	-	-	8.0			
t <sub>d(ON)</sub>	Turn-on delay time	-	-	8.0	ns	$V_{DD} = 60V,$ $I_{D} = 400mA,$	
t <sub>r</sub>	Fall time	-	-	12	113	$R_{gen} = 25\Omega$	
t <sub>d(OFF)</sub>	Turn-off delay time	-	-	18			
V <sub>SD</sub>	Diode forward voltage drop	-	1.2	-	V	$V_{_{\rm GS}}$ = 0V, I $_{_{\rm SD}}$ = 250mA	

Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

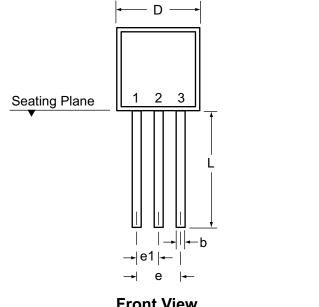
2. All A.C. parameters sample tested.

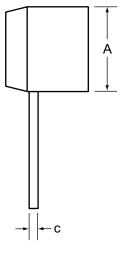
## **Switching Waveforms and Test Circuit**



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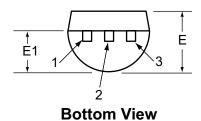
## 3-Lead TO-92 Package Outline (L)





**Front View** 

Side View



Symbol		Α	b	С	D	E	E1	е	e1	L
Dimensions (inches)	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

\* This dimension is not specified in the JEDEC drawing.

† This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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